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¹Institut Néel, France; ²CEA-Leti, France; ³CEA-IRIG, France

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¹Peter Grünberg Institute, Germany; ²RWTH Aachen University, Germany

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¹The University of Texas at Austin, United States; ²Tsinghua University, China

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¹University of Stuttgart, Germany; ²Peter Grünberg Institute, Germany; ³IHP - Leibniz Institute for High Performance Microelectronics, Germany; ⁴Roma Tre University, Italy; ⁵University of Erlangen-Nuremberg, Germany

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¹University of Stuttgart, Germany; ²University of Erlangen-Nuremberg, Germany

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¹University of Southern California, United States; ²California Institute of Technology, United States

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¹IMS CHIPS, Germany; ²OSYPKA AG, Germany; ³Philips Research Eindhoven, The Netherlands

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¹STMicroelectronics, France; ²INSA Lyon, France; ³CEA-Leti, France; ⁴STMicroelectronics, United Kingdom

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¹Pohang University of Science and Technology, Korea; ²Samsung Electronics Co., Ltd., Korea

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¹Université Grenoble Alpes, IMEP-LAHC, France; ²IBM Research Zürich, Switzerland

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Advanced CMOS Modeling

Date: Tuesday, September 20, 2022
Time: 17:30 - 18:30
Room: Aula 1D
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Viktor Sverdlov, TU Wien

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¹École Polytechnique Fédérale de Lausanne, Switzerland; ²GlobalFoundries, Germany

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Room: Aula 1F
Chair(s): Denis Rideau, STMicroelectronics
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¹Institut d'Optique Graduate School, France; ²STMicroelectronics, France

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Reliability & Characterization

Date: Tuesday, September 20, 2022
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¹IBM T.J. Watson Research Center, United States; ²IBM Research, United States

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¹IBM Research Zürich, Switzerland; ²ETH Zürich, Switzerland

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Room: Aula 1F

Chair(s): Jean-Michel Sallese, EPFL
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¹Peking University, China; ²Shanghai Institute of Microsystem and Information Technology, CAS, China;

³The Chinese University of Hong Kong, China; ⁴The Hong Kong University of Science and Technology, China

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Frederic Allibert, SOITEC, France

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¹III-V Lab, France; ²University of Bordeaux, France; ³Nokia Bell Labs, France

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¹University of Ulsan, Korea; ²Korea Advanced Nano Fab Center, Korea

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¹CEA-Leti, France; ²Soitec, France

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Date: Wednesday, September 21, 2022

Time: 15:20 - 16:40

Room: Aula 1F

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¹University of Stuttgart, Germany; ²Rochester Institute of Technology, United States

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¹Technische Universität Wien, Austria; ²Silvaco Europe Ltd., United Kingdom

Advanced Devices & VLSI Processing

Date: Wednesday, September 21, 2022

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Room: Aula 1F

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¹GlobalFoundries, Germany; ²Technische Universität Dresden, Germany

A Novel Energy-Efficient Salicide-Enhanced Tunnel Device Technology Based on 300 mm Foundry Platform Towards AIoT Applications N/A

Kaifeng Wang¹, Qianqian Huang^{1,3,4}, Yongqin Wu², Ye Ren², Renjie Wei¹, Zhixuan Wang¹, Libo Yang¹,
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Defects & Traps Modeling

Date: Wednesday, September 21, 2022
Time: 9:20 - 10:50
Room: Aula 1D
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GaN HEMT Technology

Date: Wednesday, September 21, 2022
Time: 14:20 - 16:00
Room: Aula 1F
Chair(s): Susanna Reggiani, University of Bologna
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